## LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A substrate processing apparatus, comprising:

a first processing chamber capable of being isolated from an external atmosphere, said first processing chamber including a liquid chemical processing part for performing liquid chemical process on substrates by a structure that enables dipping substrates into a liquid chemical stored in liquid chemical baths, and the atmosphere within said first processing chamber being continuously replaced by an inert gas;

a second processing chamber capable of being isolated from an external atmosphere as well as from the atmosphere in said first processing chamber, said second processing chamber including a pure water processing part for performing pure water process on substrates by dipping substrates into pure water stored in rinse baths, and a dry processing part for performing dry process on substrates drawn up from said rinse baths, and the atmosphere within said second processing chamber being continuously replaced by an inert gas, with the dry process being effected by supplying a drying gas which is different from the inert gas;

a first opening provided to an upper portion of said first processing chamber, said first opening allowing substrates to pass therethrough;

a first shutter member for exposing and blocking said first opening;

a second opening provided to an upper portion of said second processing chamber, said second opening allowing substrates to pass therethrough;

a second shutter member for exposing and blocking said second opening;

a third opening provided between said first and second processing chambers, said third opening allowing substrates to pass therethrough;

a third shutter member for exposing and blocking said third opening, said third shutter member being effective in a closed state thereof to isolate the atmosphere within said first processing chamber from the atmosphere within said second processing chamber;

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